IN THE CLAIMS

Presented below are all of the pending claims, with status identifiers as promulgated in the Interim Revised Format directions.

1. (Cancelled).

2. (Currently amended) ~~The apparatus of claim 1~~ An apparatus, comprising:

a metal-oxide-semiconductor transistor;

a metallic gate electrode coupled to a diffused gate region of said metal-oxide-semiconductor transistor and to a positive voltage source; and

a metallic source electrode and a metallic drain electrode coupled to said metal-oxide-semiconductor transistor and to each other and to a negative voltage source, wherein said metal-oxide-semiconductor transistor includes ~~a~~ the diffused gate region formed from material with a work function less than – 0.56 volts.

3. (Currently amended) The apparatus of claim 2, wherein said ~~diffused gate region~~ material of said diffused gate region is platinum silicate.

4. (Currently amended) The apparatus of claim 2, wherein said ~~diffused gate region~~ material of said diffused gate region is selected

from the group consisting of tantalum nitrate, iridium, nickel, and arsenic.

5. (Currently amended) The apparatus of claim ~~1~~ 2, wherein said metal-oxide-semiconductor transistor includes a heavily-doped substrate area.

6. (Currently amended) The apparatus of claim ~~1~~ 2, wherein said metal-oxide-semiconductor transistor is a p-channel device.

7. (Currently amended) The apparatus of claim ~~1~~ 2, wherein said metal-oxide-transistor is an n-channel device.

15. through 19. (Cancelled)

20. (Currently amended) An apparatus, comprising:

a metallic gate electrode to couple to a positive power supply voltage;

a diffused gate region ~~with a~~ formed from a material whose work function is less than minus 0.56 volts;

a gate insulator area;

a channel area coupled to said gate insulator area;

a diffused drain area coupled to said channel area; and

a diffused source area coupled to said channel area.

21. (Previously added) The apparatus of claim 20, wherein said material is platinum silicate.

22. (Previously added) The apparatus of claim 20, wherein said material is selected from the group consisting of tantalum nitrate, iridium, nickel, and arsenic.

23. (Previously added) The apparatus of claim 20, further comprising a substrate which is heavily-doped.